Class : XIIth Date : DAILY PRACTICE PROBLEMS

Solutions

Subject : PHYSICS DPP No. : 8

Topic :- Semiconductor electronics: materials, devies and simple circuits

1 (c)

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If lattice constant of semiconductor is decreased, then E_c and E_v decrease, but E_g increases. (c)

We know that resistance of conductor is directly proportional to temperature (*ie*, $R \propto \Delta t$), while resistance of semiconductor is inversely proportional to temperature (*ie*, $R \propto \frac{1}{\Lambda t}$).

Therefore, it is clear that resistance of conductor decreases with decrease in temperature of *vice-versa*, while in case of semiconductor, resistance increase with decrease in temperature of *vice-versa*.

Since, copper is pure conductor and germanium is a semiconductor hence, due to decrease in temperature, resistance of conductor decreases while that of semiconductor increases.

(a)

(a)

(b)

Density
$$\rho = \frac{nA}{N(a)^3}$$

where $n = 2$ for bcc structure, $A = 39 \times 10^{-3} kg$
 $N = 6.02 \times 10^{23}$, $a = \frac{2}{\sqrt{3}} d = \frac{2}{\sqrt{3}} \times (4.525 \times 10^{-10})m$

[d = nearest neighbor distance = distance between centres of two neighbouring atoms= $\frac{\sqrt{3}}{2}a]$

On putting the values we get $\rho = 907$

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In *p*-type semiconductor holes are majority carriers and electrons are minority carriers.

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It is the symbol of 'NOR' gate

6 **(c)**

For hexagonal crystal structure, $a = b \neq c$ and $\alpha = \beta = 90^{\circ}$ but $\gamma = 120^{\circ}$.

8 **(d)**

Arsenic has five valence electrons, so it a donor impurity. Hence *X* becomes *N*-type semiconductor. Indium has only three outer electrons, so it is an acceptor impurity. Hence *Y* becomes *P*-type semiconductor. Also *N* (*i.e.,X*) is connected to positive terminal of battery and P(i.e.,Y) is connected to negative terminal of battery so *PN*-junction is reverse

biased

9 **(b)**

The difference in the variation of resistance with temperature in a metal and semiconductor is caused due to the difference in the variation of the number of charge carriers with temperature.

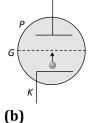
10 **(a)**

The potential of *P*-side is more negative that of *N*-side, hence diode is in reverse biasing. In reverse biasing it acts as open circuit, hence no current flows

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(b)

When grid is given positive potential more electrons will cross the grid to reach the positive plate *P*. Hence current increases



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This is operational or OP-inverting amplifier

$$A = \frac{V_0}{V_i} = -\frac{R_f}{R_i}$$

Given $V_i = 1V$, $R_f = 10k\Omega$, $R_i = 1k\Omega$
 $\therefore V_0 = -V_i \frac{R_f}{R_i} = -1 \times \frac{10}{1} \Rightarrow V_0 = -10V$

 V_0 is negative because V_{input} is +1V (positive)

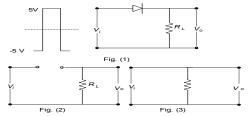
 $V_i < C$

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(d) For



the diode is reverse biased and hence offer infinite resistance, so circuit would be like as shown in Fig. (2) and $V_o = 0$.



For $V_i > 0$, the diode is forward biased and circuit would be as shown in Fig. (3) and $V_o = V_i$

Hence, the optical (d) is correct.

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(b)

Maximum load current $I_m = \frac{V_m}{r_f + R_L} = \frac{50\sqrt{2}V}{(20 + 980)\Omega}$ = 70.7 mA \therefore Mean load current. $I_{DC} = \frac{2I_m}{\pi} = \frac{2 \times 70.7}{\pi} = 45$ mA

16 **(a)**

The input of OR gate is *A* and $\overline{(A \cdot B)}$. Hence $Y = A + \overline{(A \cdot B)}$.

17 **(d)**

The given truth table follows a NAND gate whose output is 1 only if at least one of its input is zero. Its Boolean expression is

 $Y = \overline{A \cdot B}$ So that $\overline{1 \cdot 1} = \overline{1} = 0$ $\overline{1 \cdot 0} = \overline{0} = 1$ $\overline{0 \cdot 1} = \overline{0} = 1$ $\overline{0 \cdot 0} = \overline{0} = 1$

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Tourmaline is the dichroic crystal

19 **(d)**

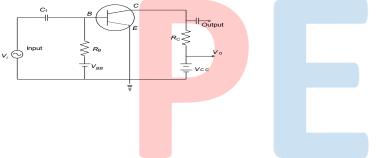
(d)

(d)

Ionic bond is a type of chemical bond based on electrostatic forces between two oppositely charged ions. Bond between NaCl, CsCl and LiF are ionic, while H_2O forms a covalent bond.

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In CE amplifier, the input signal is applied across base-emitter junction as shown in the figure below.



ANSWER-KEY										
Q.	1	2	3	4	5	6	7	8	9	10
A.	C	C	А	А	В	С	А	D	В	A
Q.	11	12	13	14	15	16	17	18	19	20
A.	В	С	В	D	В	А	D	D	D	D

